

L Number	Hits	Search Text	DB	Time stamp
1	3371	"mold compound" or "mold resin"	USPAT; US-PGPUB	2003/08/18 13:19
2	762	passivation and mounting and (etching or patterning) and (polysilicon or polycrystalline)	USPAT; US-PGPUB	2003/08/18 12:50
3	7	("mold compound" or "mold resin") and (passivation and mounting and (etching or patterning) and (polysilicon or polycrystalline))	USPAT; US-PGPUB	2003/08/18 12:48
4	2436	oxide and mounting and (etching or patterning) and (polysilicon or polycrystalline)	USPAT; US-PGPUB	2003/08/18 14:37
5	23	("mold compound" or "mold resin") and (oxide and mounting and (etching or patterning) and (polysilicon or polycrystalline))	USPAT; US-PGPUB	2003/08/18 12:50
6	164422	@ad>20020128 or @rlad>20020128	USPAT; US-PGPUB	2003/08/18 12:50
7	21	((("mold compound" or "mold resin") and (oxide and mounting and (etching or patterning) and (polysilicon or polycrystalline))) not (@ad>20020128 or @rlad>20020128))	USPAT; US-PGPUB	2003/08/18 12:54
8	12854	((opening or hole or trench or recess) with (polysilicon or polycrystalline))	USPAT; US-PGPUB	2003/08/18 12:57
9	1	("mold compound" or "mold resin") with (((opening or hole or trench or recess) with (polysilicon or polycrystalline)))	USPAT; US-PGPUB	2003/08/18 12:55
10	20619	((etching or patterning) with (polysilicon or polycrystalline))	USPAT; US-PGPUB	2003/08/18 12:56
11	0	("mold compound" or "mold resin") with (((etching or patterning) with (polysilicon or polycrystalline)))	USPAT; US-PGPUB	2003/08/18 12:56
12	1	("mold compound" or "mold resin") same (((etching or patterning) with (polysilicon or polycrystalline)))	USPAT; US-PGPUB	2003/08/18 12:56
13	246	((opening or hole or trench or recess) with ("mold compound" or "mold resin"))	USPAT; US-PGPUB	2003/08/18 14:37
14	2465	passivation and mounting and (etching or patterning)	USPAT; US-PGPUB	2003/08/18 12:58
15	26	((opening or hole or trench or recess) with ("mold compound" or "mold resin")) and (passivation and mounting and (etching or patterning))	USPAT; US-PGPUB	2003/08/18 12:58
16	25	((opening or hole or trench or recess) with ("mold compound" or "mold resin")) and (passivation and mounting and (etching or patterning)) not (@ad>20020128 or @rlad>20020128)	USPAT; US-PGPUB	2003/08/18 12:58
17	68550	438/\$.ccls.	USPAT; US-PGPUB	2003/08/18 13:01
18	43	((opening or hole or trench or recess) with ("mold compound" or "mold resin")) and 438/\$.ccls.	USPAT; US-PGPUB	2003/08/18 13:01
19	3	("mold compound" or "mold resin") with polysilicon	USPAT; US-PGPUB	2003/08/18 13:20
20	6	("mold compound" or "mold resin") same polysilicon	USPAT; US-PGPUB	2003/08/18 14:07
21	4723	CTE	USPAT; US-PGPUB	2003/08/18 14:08
22	642	438/\$.ccls. and CTE	USPAT; US-PGPUB	2003/08/18 14:08
24	281	((opening or hole or trench or recess) with ("mold compound" or "mold resin"))	EPO; JPO; DERWENT	2003/08/18 14:38
23	18	oxide and mounting and (etching or patterning) and (polysilicon or polycrystalline)	EPO; JPO; DERWENT	2003/08/18 14:38
-	636	438/124.ccls.	USPAT; US-PGPUB	2003/08/12 13:33
-	19	438/124.ccls. and (passivation and mounting and (etching or patterning))	USPAT; US-PGPUB	2003/08/18 10:47
-	1	438/127.ccls.	USPAT; US-PGPUB	2003/08/12 13:33
-	0	(passivation and mounting and (etching or patterning)) and 438/127.ccls.	USPAT; US-PGPUB	2003/08/18 10:53

-	209	438/129.ccls.	USPAT; US-PGPUB	2003/08/12 13:33
-	2	((passivation and mounting and (etching or patterning)) and 438/129.ccls.	USPAT; US-PGPUB	2003/08/18 10:55
-	610	((passivation and mounting and (etching or patterning)) and 438/\$.ccls.	USPAT; US-PGPUB	2003/08/12 13:36
-	4826	"interface layer"	USPAT; US-PGPUB	2003/08/12 13:36
-	8	((passivation and mounting and (etching or patterning)) and 438/\$.ccls.) and "interface layer"	USPAT; US-PGPUB	2003/08/18 10:56
-	83751	polysilicon or polycrystalline	USPAT; US-PGPUB	2003/08/12 13:39
-	551	((passivation and mounting and (etching or patterning)) and (polysilicon or polycrystalline)	USPAT; US-PGPUB	2003/08/12 13:39
-	235	438/\$.ccls. and ((passivation and mounting and (etching or patterning)) and (polysilicon or polycrystalline))	USPAT; US-PGPUB	2003/08/18 10:12
-	212	(438/\$.ccls. and ((passivation and mounting and (etching or patterning)) and (polysilicon or polycrystalline))) not (@ad>20020128 or @rlad>20020128)	USPAT; US-PGPUB	2003/08/18 10:13
-	46	438/124.ccls. and (oxide and mounting and (etching or patterning))	USPAT; US-PGPUB	2003/08/18 10:48
-	40	(438/124.ccls. and (oxide and mounting and (etching or patterning))) not (@ad>20020128 or @rlad>20020128)	USPAT; US-PGPUB	2003/08/18 10:48
-	42	(oxide and mounting and (etching or patterning)) and 438/127.ccls.	USPAT; US-PGPUB	2003/08/18 10:54
-	39	((oxide and mounting and (etching or patterning)) and 438/127.ccls.) not (@ad>20020128 or @rlad>20020128)	USPAT; US-PGPUB	2003/08/18 10:54
-	9	(oxide and mounting and (etching or patterning)) and 438/129.ccls.	USPAT; US-PGPUB	2003/08/18 10:55
-	25	((oxide and mounting and (etching or patterning)) and 438/\$.ccls.) and "interface layer"	USPAT; US-PGPUB	2003/08/18 10:56
-	22	((oxide and mounting and (etching or patterning)) and 438/\$.ccls.) and "interface layer") not (@ad>20020128 or @rlad>20020128)	USPAT; US-PGPUB	2003/08/18 10:57
-	0	"stress relieve interface" with (polysilicon or polycrystalline)	USPAT; US-PGPUB	2003/08/18 11:05
-	0	"stress relieve interface"	USPAT; US-PGPUB	2003/08/18 12:47